



3N100-FC

Power MOSFET

3.0A, 1000V N-CHANNEL POWER MOSFET

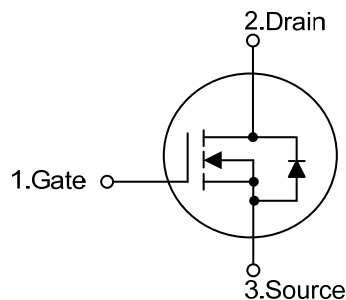
DESCRIPTION

The UTC 3N100-FC provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

FEATURES

- * $R_{DS(ON)} \leq 9.0 \Omega$ @ $V_{GS}=10V$, $I_D=1.5A$
- * Low Reverse Transfer Capacitance
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, High Ruggedness

SYMBOL

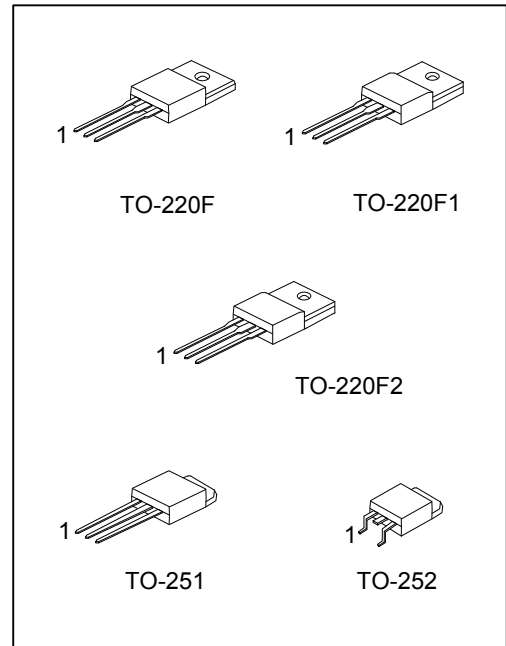


ORDERING INFORMATION

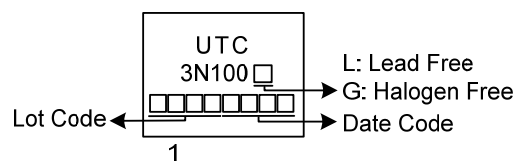
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
3N100L-TF1-T	3N100G-TF1-T	TO-220F1	G	D	S	Tube
3N100L-TF2-T	3N100G-TF2-T	TO-220F2	G	D	S	Tube
3N100L-TF3-T	3N100G-TF3-T	TO-220F	G	D	S	Tube
3N100L-TM3-T	3N100G-TM3-T	TO-251	G	D	S	Tube
3N100L-TN3-R	3N100G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

3N100G-TF1-T (1)Packing Type (2)Package Type (3)Green Package	(1) T: Tube, R: Tape Reel (2) TF1: TO-220F1, TF2: TO-220F2, TF3: TO-220F TM3: TO-251, TN3: TO-252 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	1000	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	3	A
	Pulsed (Note 2)	I_{DM}	6	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	93	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.1	V/ns
Power Dissipation	TO-220F/TO-220F1	P_D	18	W
	TO-220F2			
	TO-251/TO-252		42	W
Junction Temperature		T_J	+150	$^{\circ}\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L=30\text{mH}$, $I_{AS}=2.5\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, Starting $T_J = 25^{\circ}\text{C}$

4. $I_{SD}\leq 3.0\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J = 25^{\circ}\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220F/TO-220F1	θ_{JA}	62.5	$^{\circ}\text{C}/\text{W}$
	TO-220F2			
	TO-251/TO-252		110	$^{\circ}\text{C}/\text{W}$
Junction to Case	TO-220F/TO-220F1	θ_{JC}	6.94	$^{\circ}\text{C}/\text{W}$
	TO-220F2			
	TO-251/TO-252		2.9 (Note)	$^{\circ}\text{C}/\text{W}$

Note: Device mounted on FR-4 substrate P_C board, 2oz copper, with 1inch square copper plate.

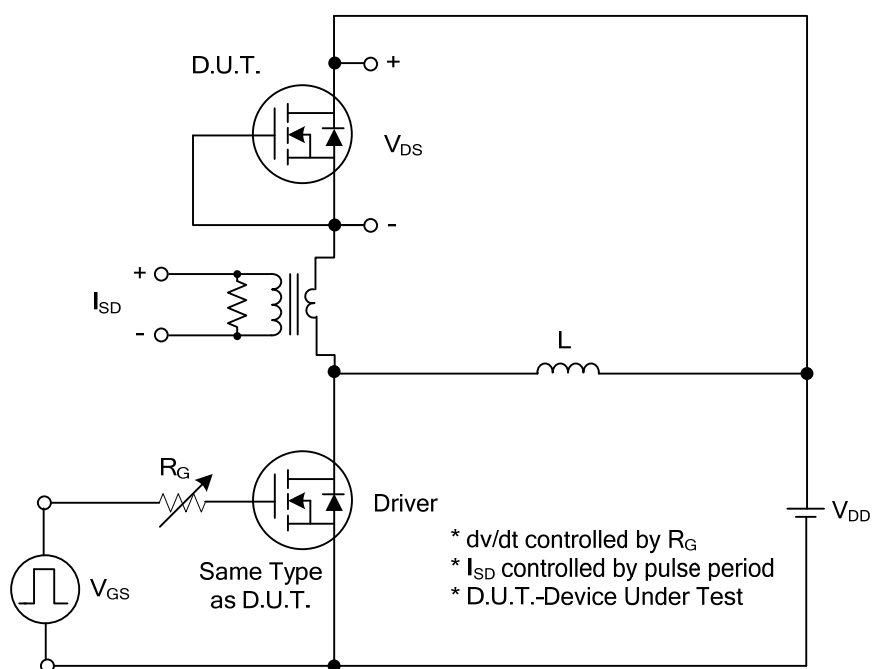
■ ELECTRICAL CHARACTERISTICS (T_J =25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	1000			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =1000V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	3.0		5.0	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =1.5A			9.0	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1MHz		385		pF
Output Capacitance	C _{OSS}			42		pF
Reverse Transfer Capacitance	C _{RSS}			2		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge (Note 1)	Q _G	V _{DS} =800V, V _{GS} =10V, I _D =3A I _G =1mA (Note 1, 2)		13		nC
Gate-Source Charge	Q _{GS}			6		nC
Gate-Drain Charge	Q _{GD}			2		nC
Turn-On Delay Time (Note 1)	t _{D(ON)}	V _{DD} =100V, V _{GS} =10V, I _D =3A, R _G =25Ω (Note 1, 2)		8		ns
Turn-On Rise Time	t _R			15		ns
Turn-Off Delay Time	t _{D(OFF)}			20		ns
Turn-Off Fall Time	t _F			30		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I _S				3	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				6	A
Drain-Source Diode Forward Voltage (Note 1)	V _{SD}	I _S =3A, V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)	t _{rr}	I _S =3A, V _{GS} =0V,		840		nS
Body Diode Reverse Recovery Charge	Q _{rr}	dI _F /dt=100A/μs		5.6		μC

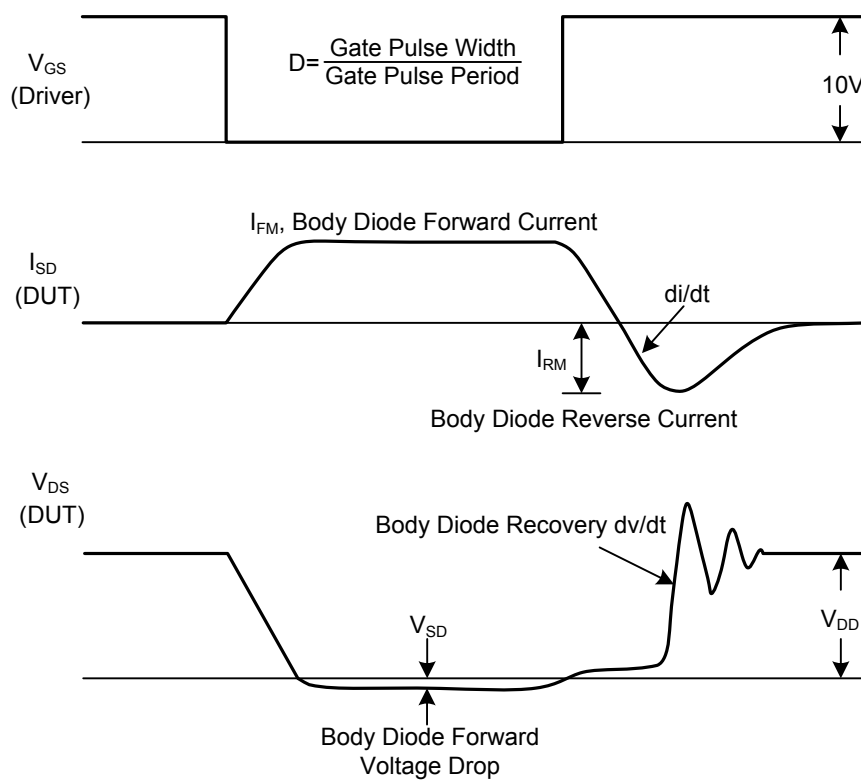
Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

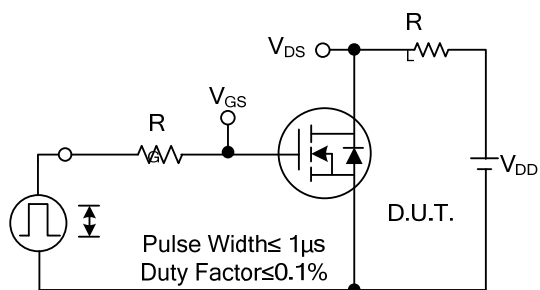


Peak Diode Recovery dv/dt Test Circuit

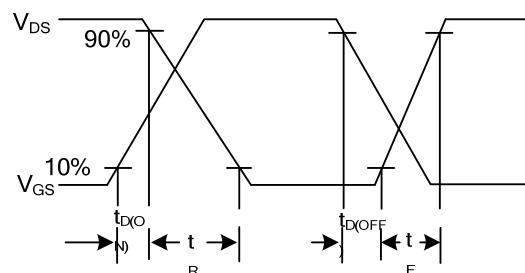


Peak Diode Recovery dv/dt Waveforms

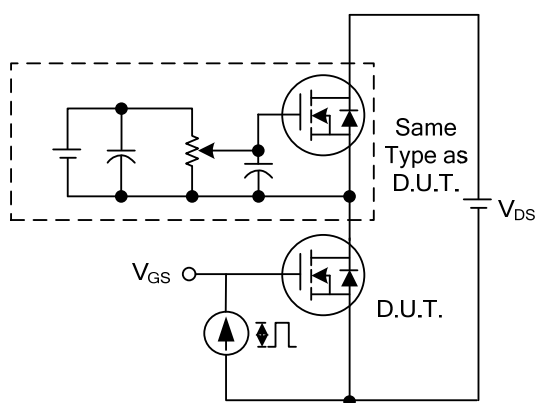
■ TEST CIRCUITS AND WAVEFORMS



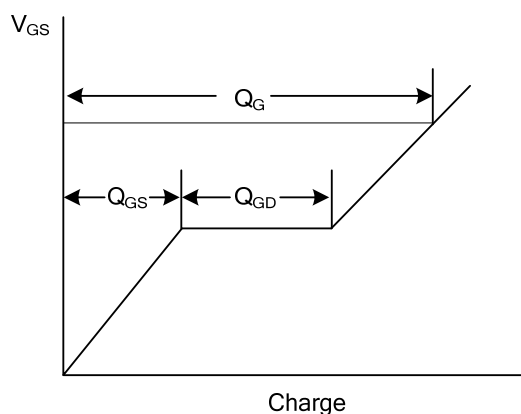
Switching Test Circuit



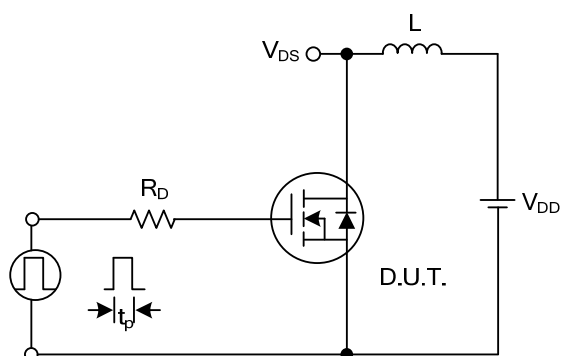
Switching Waveforms



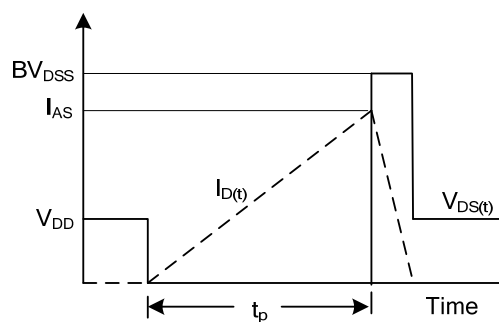
Gate Charge Test Circuit



Gate Charge Waveform

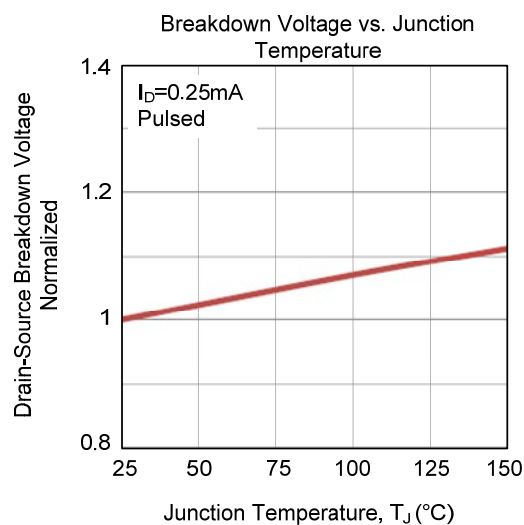
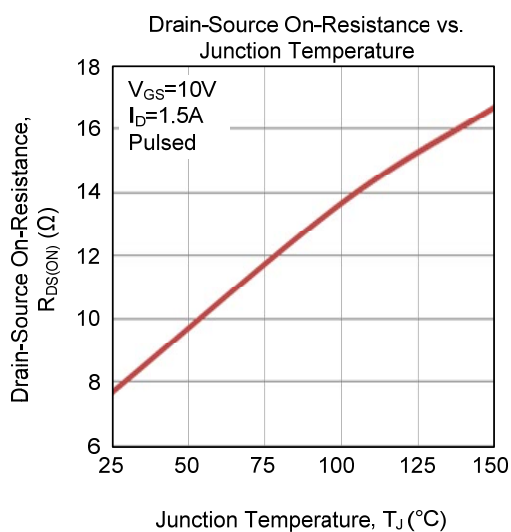
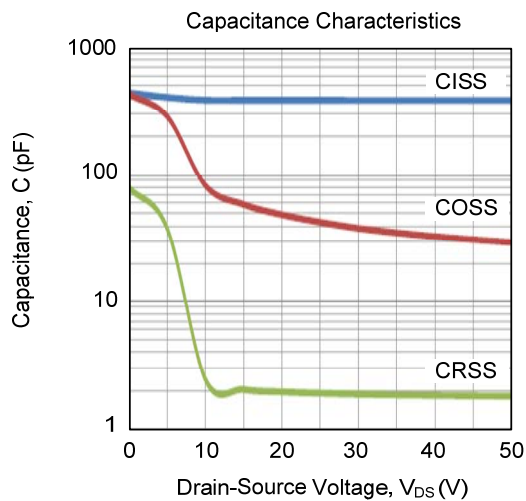
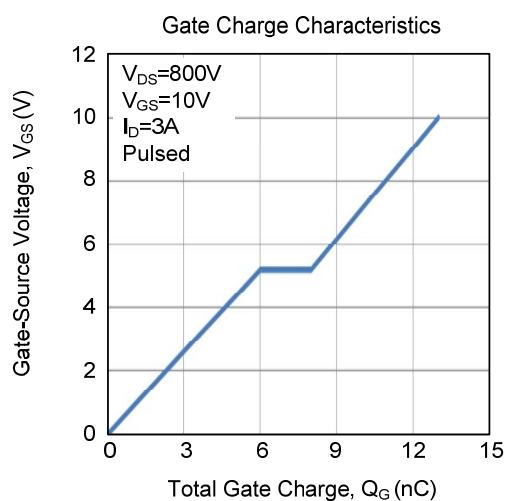
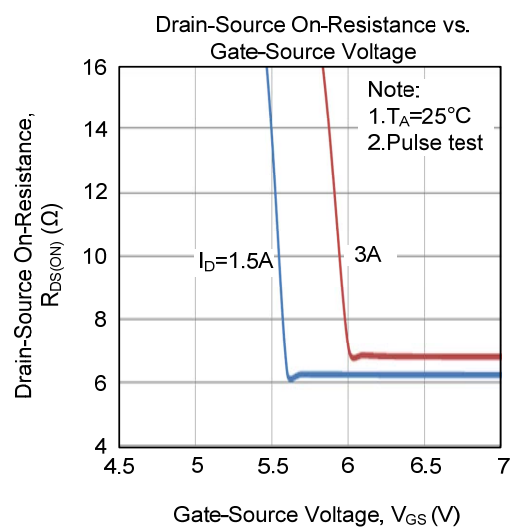
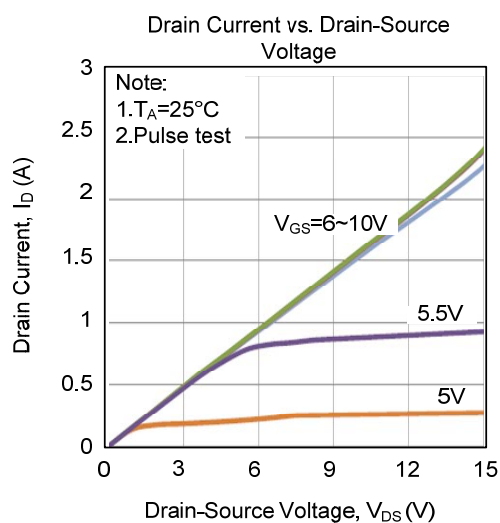


Unclamped Inductive Switching Test Circuit

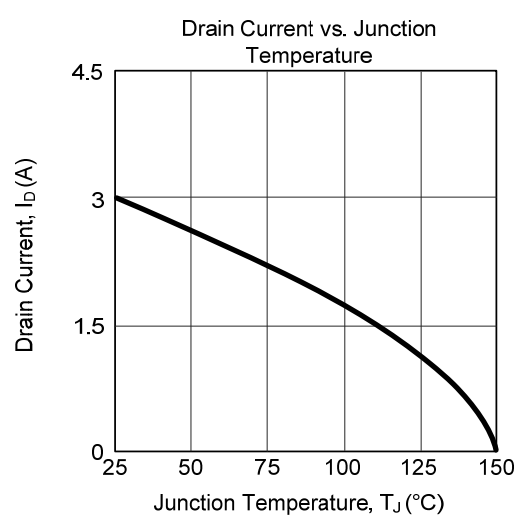
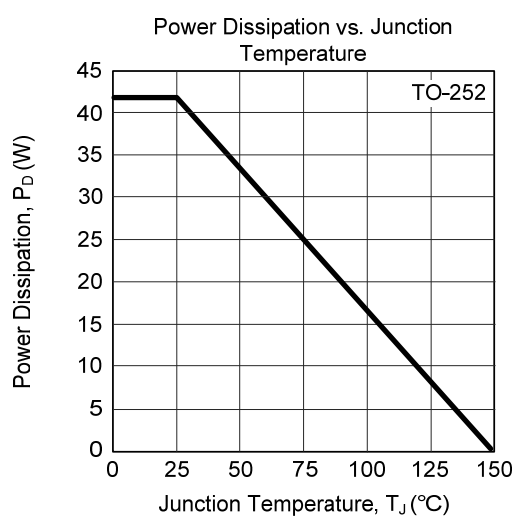
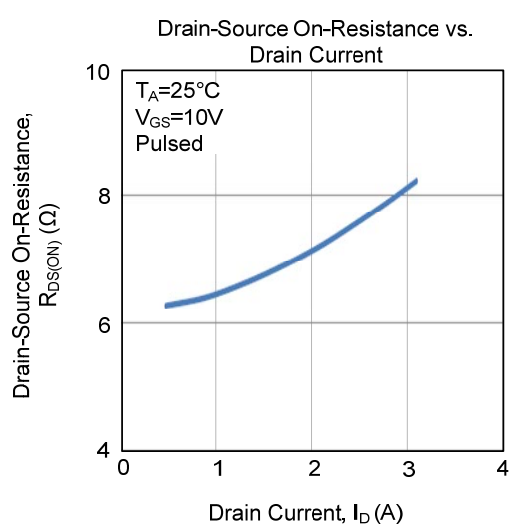
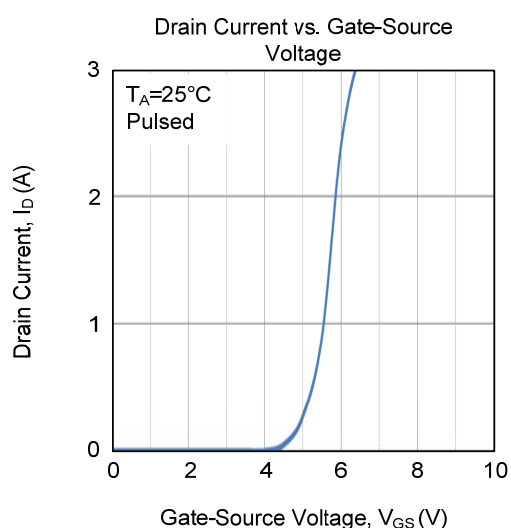
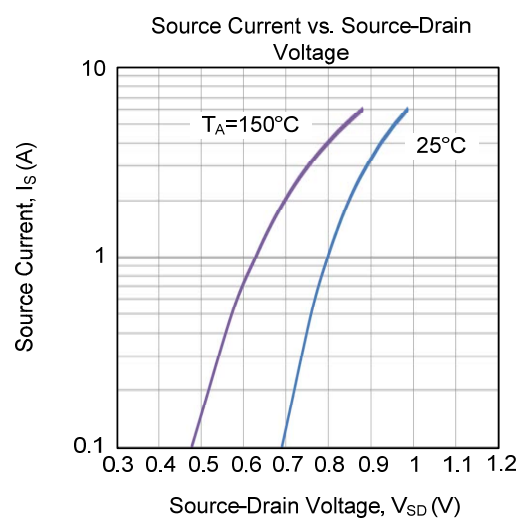
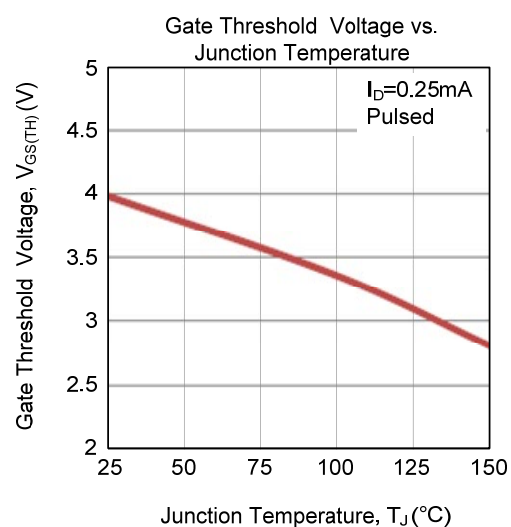


Unclamped Inductive Switching Waveforms

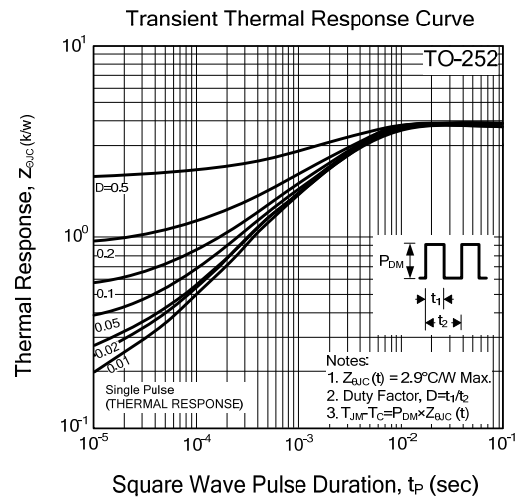
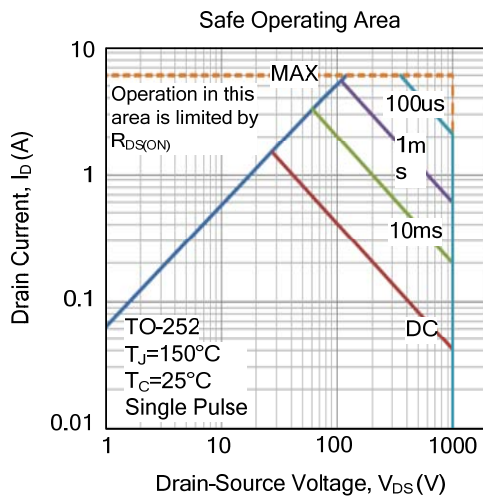
TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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